

Serial No.: 09/848,997
Group Art Unit: 2822

AMENDMENT**IN THE CLAIMS:**

- Please replace pending claim 7 with the following clean amended claims 7:

7. (Amended) A method for planarization of low dielectric constant ILD layers on a semiconductor wafer comprising:
providing an oven having a rotatable wafer holder provided therein ;
placing the semiconductor wafer on the wafer holder;
rotating the wafer holder with the semiconductor wafer thereon;
spining on the low dielectric constant ILD material on to the semiconductor wafer in the oven;
soft baking the low dielectric constant ILD material at a soft bake temperature in the oven;
holding the low dielectric constant ILD material at a temperature below the hard bake temperature in the oven;
applying mechanical pressure to the ILD layer on the semiconductor wafer using a mechanical device to apply rotating pressure to the ILD layer in the oven;
applying heat to the ILD layer on the semiconductor wafer through the mechanical device simultaneously with the applying the mechanical pressure in the oven;
hard baking the low dielectric constant ILD material at a hard bake temperature in the oven;
cooling the low dielectric constant ILD material in the oven; and
annealing the low dielectric constant ILD material in the oven.